TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MBL6125SFT, TC7MBL6125SFK, TC7MBL6125SFTG TC7MBL6126SFT, TC7MBL6126SFK, TC7MBL6126SFTG

Quad Low Voltage/Low Capacitance Bus Switch

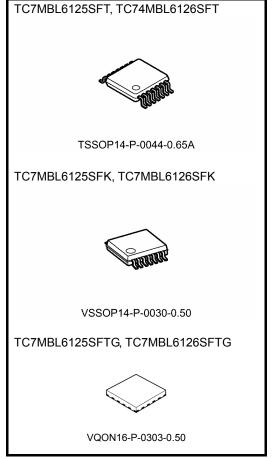
TC7MBL6125S/6126S is low voltage CMOS 4-bit Bus Switch. The low on resistance of the switch allows connections to be made with minimal propagation delay and while maintaining CMOS low power dissipation.

The TC7MBL6125S requires the output enable (\overline{OE}) input to be set high to place the output into the high impedance state, whereas the TC7MBL6126S requires the output enable (OE) input to be set low to place the output into high impedance.

All inputs are equipped with protection circuits against static discharge.

Features

- Operating voltage: $V_{CC} = 1.65 \sim 3.6 \text{ V}$
- Low capacitance : CI/O=12 pF Switch On (typ.) @3 V
- Low on resistance: $R_{ON} = 9 \Omega$ (typ.) @3 V
- ESD performance: Machine model $\geq \pm 200 \text{ V}$ Human body model $\geq \pm 2000 \text{ V}$
- Power down protection for inputs
- Package: TSSOP14,VSSOP (US14), VQON16



Weight

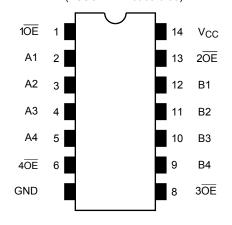
TSSOP14-P-0044-0.65A : 0.06 g (typ.) VSSOP14-P-0030-0.50 : 0.02 g (typ.) VQON16-P-0303-0.50 : 0.013 g(typ.)

Note: When mounting VQON package, the type of recommended flux is RA or RMA.

Pin Assignment (top view)

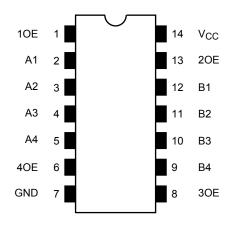
TC7MBL6125S

FT (TSSOP14-P-0044-0.65A) FK (VSSOP14-P-0030-0.50)

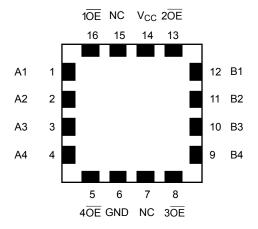


TC7MBL6126S

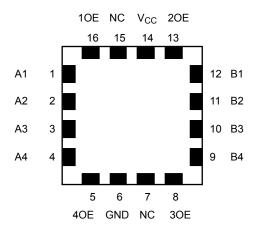
FT (TSSOP14-P-0044-0.65A) FK (VSSOP14-P-0030-0.50)



FTG (VQON16-P-0303-0.50)



FTG (VQON16-P-0303-0.50)

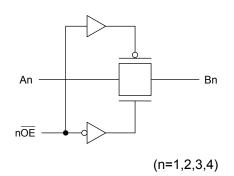


Truth Table

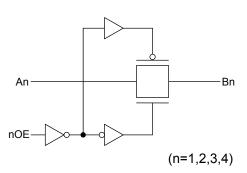
Inputs (6125S)	Inputs (6126S)	Function
ŌĒ	OE	Tunction
L	Н	A port = B port
Н	L	Disconnect

System Diagram

TC7MBL6125S



TC7MBL6126S





Absolute Maximum Ratings (Note)

Chara	cteristic	Symbol	Rating	Unit
Power supply rang	е	V_{CC}	-0.5~4.6	V
Control pin input vo	oltage	V _{IN}	-0.5~4.6	V
Switch terminal I/O	voltage	VS	-0.5~V _{CC} + 0.5	V
Clump diode	Control input pin	luz	-50	mA
current	Switch terminal	lik	±50	mA
Switch I/O current		IS	50	mA
Power dissipation		P_{D}	180	mW
DC V _{CC} /GND curre	ent	I _{CC} /I _{GND}	±100	mA
Storage temperatu	re	T _{stg}	-65~150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristic	Symbol	Rating	Unit
Power supply voltage	V_{CC}	1.65~3.6	V
Control pin input voltage	V _{IN}	0~3.6	V
Switch I/O voltage	Vs	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10	ns/V

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.



Electrical Characteristics

DC Characteristics ($Ta = -40 \sim 85$ °C)

Parame	eter	Symbol	Test Condition V _{CC} (V)		Min	Тур.	Max	Unit	
Input voltage	"H" level	V _{IH}	_	— 1.6		0.7 × V _{CC}	_		V
input voitage	"L" level	V _{IL}	_		1.65~3.6	_		0.3 × V _{CC}	V
Input leakage cur	rent (OE, S)		V _{IN} = 0~3.6V		1.65~3.6			±1.0	μΑ
Power off leakage	e current		OE , OE = 0~3.6 V		0	_	_	1.0	μА
Off-state leakage (switch off)	current		A, B = $0 \sim V_{CC}$, $\overline{OE} = V_{CC}(6125S)$, OE=GND(6126S)		1.65~3.6	_	_	±1.0	μΑ
			$V_{IS} = 0 \text{ V}, I_{IS} = 30 \text{ mA}$ (Note1)		3.0	_	9	13	
		$V_{IS} = 3.0 \text{ V}, I_{IS} = 30 \text{ mA}$	(Note1)	3.0	_	15	20		
On resistance		V _{IS} = 2.4 V, I _{IS} = 15 mA	(Note1)	3.0	_	19	27	0	
(Note2)		V _{IS} = 0 V, I _{IS} = 24 mA	(Note1)	2.3	_	10	16	Ω	
			$V_{IS} = 2.3 \text{ V}, I_{IS} = 24 \text{ mA}$	(Note1)	2.3	_	17	24	
			V _{IS} = 2.0 V, I _{IS} = 15 mA	(Note1)	2.3	_	21	30	
Increase in I _{CC} po	er input		$V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0$ 3.6		3.6	_	_	10	μА

Note1: All typical values are at Ta=25°C.

Note2: Measured by the voltage drop between A and B pins at the indicated current through the switch.

On resistance is determined by the lower of the voltages on the two (A or B) pins.

AC Characteristics ($Ta = -40 \sim 85$ °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
			3.3 ± 0.3	_	6	
Output enable time	t _{pZL}	Figure 1, Figure 2	2.5 ± 0.2	_	7	ns
t _{pZF}		ZH		_	11	
			3.3 ± 0.3	_	6	
Output disable time	t _{pLZ}	Figure 1, Figure 2	2.5 ± 0.2	_	7	ns
t _{pHZ}			1.8 ± 0.15	_	11	

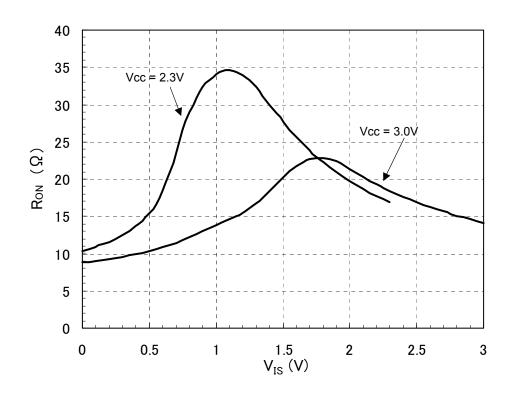
Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Тур.	Unit
Control pin input capacitance	C _{IN}			3.0	3	pF
Switch terminal capacitance	Cuo	OE =Vcc (6125S), OE=GND (6126S)	Switch Off	3.0	6	pF
Switch terminal capacitance	C _{I/O}	OE = GND (6125S), OE = Vcc (6126S)	Switch On	3.0	12	pF

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Note: This parameter is guaranteed by design

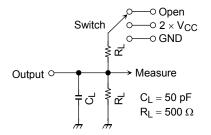
• R_{ON} Characteristic (typ.) Ta=25°C



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AC Test Circuit



Parameter	Switch
t _{pLH} , t _{pHL}	Open
t _{pLZ} , t _{pZL}	$2\times V_{CC}$
t_{pHZ} , t_{pZH}	GND

Figure 1

AC Waveform

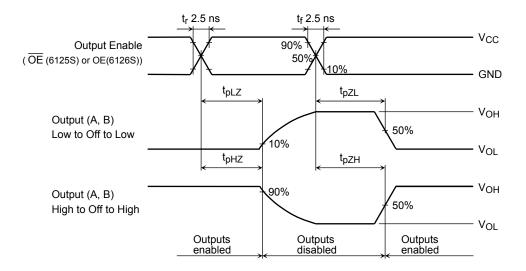


Figure 2 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Rise and Fall Times (tr / tf) of the TC7MBL6125S,6126S I/O Signals

The tr(out) and tf(out) values of the output signals are affected by the CR time constant of the input, which consists of the switch terminal capacitance ($C_{I/O}$) and the on-resistance (R_{ON}) of the input.

In practice, the tr(out) and tf(out) values are also affected by the circuit's capacitance and resistance components other than those of the TC7MBL6125S,6126S.

The tr / tf (out) values can be approximated as follows. (Figure 3 shows the test circuit.)

tr / tf out (approx) = - (
$$C_{I/O} + C_L$$
) · ($R_{DRIVE+} + R_{ON}$) · In ((($V_{OH} - V_{OL}$) - V_{M}) /($V_{OH} - V_{OL}$))

where, R_{DRIVE} is the output impedance of the previous-stage circuit.

Calculation example:

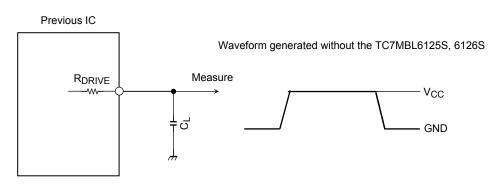
tr out (approx) = - (12 + 15)E-12 · (120 + 9) ·
$$\ln (((3.0 - 0) - 1.5)/(3.0 - 0))$$

 $\approx 2.4 \text{ ns}$

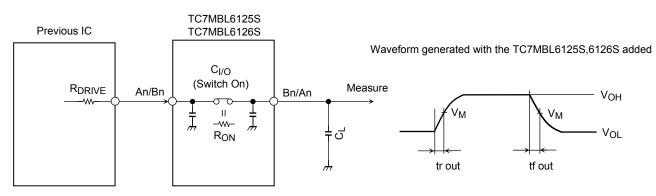
Calculation conditions:

 $V_{CC} = 3.0 \text{V} \text{ , } C_L = 15 \text{pF } \text{ , } R_{DRIVE} = 120 \Omega (\text{output impedance of the previous IC}), } V_M = 1.5 \text{V} (V_{CC} / 2)$

Output of the previous IC = digital (i.e., high-level voltage = V_{CC}; low-level voltage = GND)



R_{DRIVE} = output impedance of the previous



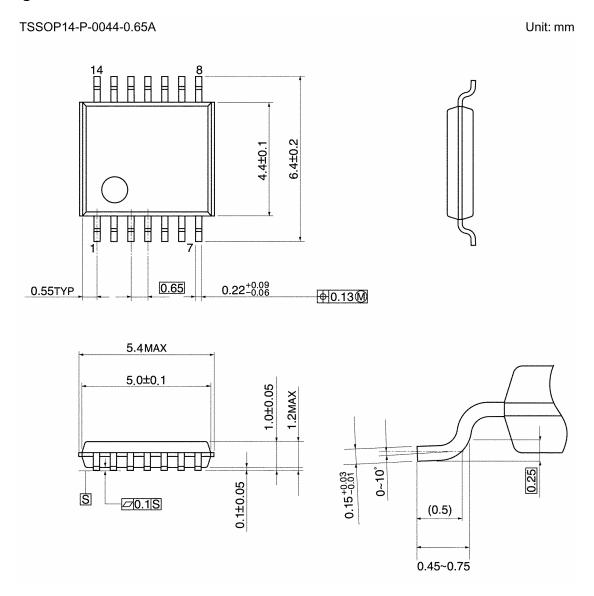
RDRIVE = output impedance of the previous

Parameter	V _{CC}						
Falameter	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 ± 0.15 V				
V_{M}	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2				

Figure 3 Test Circuit

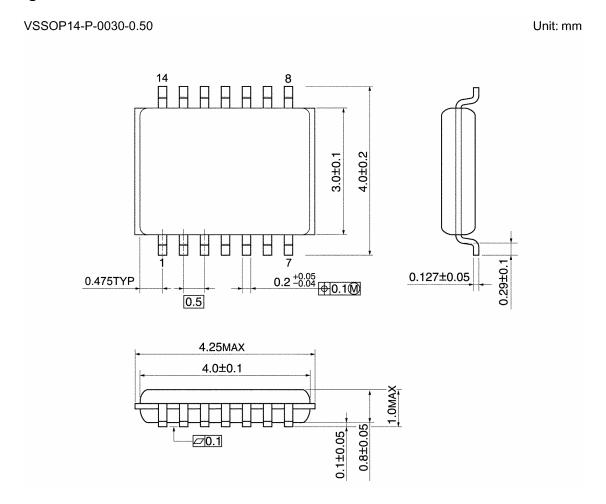


Package Dimensions



Weight: 0.06 g (typ.)

Package Dimensions

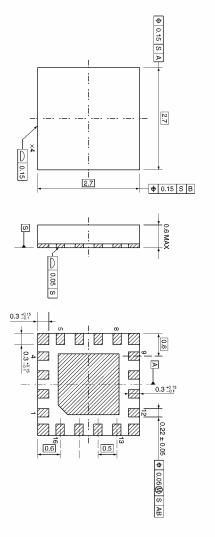


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Weight: 0.02 g (typ.)

Package Dimensions

VQON16-P-0303-0.50 Unit: mm



Weight: 0.013 g (typ.)

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20070701-EN GENERAL

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